

Notice of References Cited	Application/Control No. 10/718,070		Applicant(s)/Patent Under Reexamination HAMANN ET AL.	
	Examiner Patricia A. George		Art Unit 1765	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,943,365	09-2005	Lowrey et al.	257/3
*	B	US-6,927,410	08-2005	Chen, Bomy	257/2
*	C	US-5,536,947	07-1996	Klersy et al.	257/3
*	D	US-2004/0178401	09-2004	Ovshinsky et al.	257/002
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Jpn. J. Appl. Phys. Vol.39 (2000) 745-751;Part 1, No. 2B, 28 February 2000 Investigation of Crystallization Behavior of Sputter-Deposited Nitrogen-Doped Amorphous Ge ₂ Sb ₂ Te ₅ Thin Films Hun Seo et al
	V	
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.